

WOCSDICE 2007

31st Workshop on Compound Semiconductor Devices and Integrated Circuits held in Europe

Venice, Italy
May 20-23, 2007

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CONTACT E-MAIL: wocsdice2007@wocsdice2007.org

IMPORTANT DATES:

- October 15, 2006: Early registration and Hotel booking opening
- December 24, 2006: Deadline for short abstract submission
- January 10, 2007: Abstract acceptance notification
- January 26, 2007: Deadline for early registration
- February 27, 2007: FULL INFO sent to registered attendees
- April 10, 2007: Deadline for extended abstract (2-4 pages) submission

PRELIMINARY LIST OF INVITED SPEAKERS:

Dr. A. R. Barnes, ESTEC, ESA, Components Division
An overview of GaN microwave component research at ESA
Dr. Bertrand Bocquet, IEMN-Lille, France
THz BioMEMS for Biological investigation: technology and measurements
Dr. Philippe Bove, Picogiga International, France
Status and Future of the on Composite Substrates developed within the HYPHEN EU project
Dr. Antonio Cetronio, Selex Sistemi Integrati, Roma, Italy
"GaN-HEMT MMICs: Harnessing of a New Enabling Technology for Next Generation Systems Applications"
Dr. M. Germain, IMEC, Belgium
III-N electronics at IMEC: latest developments on SiC and large diameter Si substrates
Dr. Franco Giannini, University of Rome, Tor Vergata, Italy
New Methodologies for GaN power amplifiers design.
Dr. Berthold Hahn, OSRAM Opto-Semiconductors, Regensburg, Germany
Recent advances in GaInN LEDs
Dr. Adrian Hierro, Universidad Politécnica de Madrid - ISOM, Spain
Diluted Nitrides for IR lasing applications
Prof. D. Lippens, Prof. S. Tretyakov, IEMN, Lille, France, TKK, Helsinki, Finland
Emerging metamaterial technology: the METAMORPHOSE network of excellence
Dr. Gottfried Magerl, TU Wien, Austria - NoE "TARGET"
Review of the achievements within the TARGET Network of Excellence (issues within RF power amplifiers)
Dr. H. Lüth and M. Mikulic, Forschungszentrum Juelich, GmbH, Germany
Novel Efficient Metal-Semiconductor-Metal Photomixers
Dr. Shigeru Nakajima - Eudyna Devices Inc.
"State of the art performance for High Power & High Efficiency GaN HEMTs: a Japanese perspective"
Prof. Taiichi Otsuji, Dr. Eng., Tohoku University - Japan
Stimulated emission of terahertz radiation from a plasmon-resonant photomixer fabricated with GaAs-based heterostructure material systems
Dr. Edwin L. Piner - Nitronex Corporation
"Progress in GaN electronic devices and timeline for the completion of the overriding vision of GaN electronics: An USA perspective"
Dr. Ruediger Quay, Fraunhofer Institute of Applied Solid-State Physics (IAF), Germany
GaN HEMT: Trends in civil and military circuit applications
Dr. Dwight Streit, Northrup Grumman Space Technology
InP MMICs for Radiometer Applications
Dr. Daisuke Ueda, Dr. Masaaki Yuri, Matsushita Electric Industrial Co. Ltd., Japan
GaN-based Lasers for next-generation Blue Ray systems
Dr. J. M. Xu, Brown University, RI, USA
Arrayed Carbon Nanotubes for Uncooled IR Sensors

TOPICS COVERED:

- Wide bandgap Devices
- MW and MM-Wave Integrated Circuits
- Noise and Power Characteristics of Devices and Circuits
- Terahertz Technology
- Optoelectronic Devices and their Integration
- Novel Structures and Concepts
- Modeling and Simulation
- Technology of Devices and MMICs
- Material Growth, processing and Characterization
- RF and power devices
- Characterization of GaAs and InP-based HEMTs
- Heterojunction Bipolar Transistors
- New Materials / Device and Material characterization

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